

Silicon Diffused Power Transistor

BUJ100AT

GENERAL DESCRIPTION

High-voltage, high-speed planar-passivated npn power switching transistor in the SOT223 envelope intended for use in compact fluorescent lamps, low power electronic lighting ballasts and similar high frequency converters and inverters.

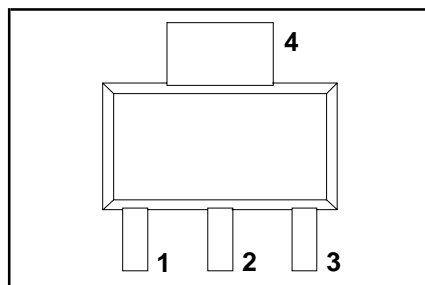
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	700	V
V_{CBO}	Collector-Base voltage (open emitter)		-	700	V
V_{CEO}	Collector-emitter voltage (open base)		-	400	V
I_C	Collector current (DC)		-	1.0	A
I_{CM}	Collector current peak value		-	2.0	A
P_{tot}	Total power dissipation	$T_{sp} \leq 25\text{ °C}$	-	6	W
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 0.75\text{ A}; I_B = 150\text{ mA}$	0.23	1.0	V
h_{FE}		$I_C = 0.75\text{ A}; V_{CE} = 5\text{ V}$	14	20	
t_{fi}	Fall time (Inductive)	$I_C = 1.0\text{ A}, I_{BON} = 200\text{ mA}$	50	70	ns

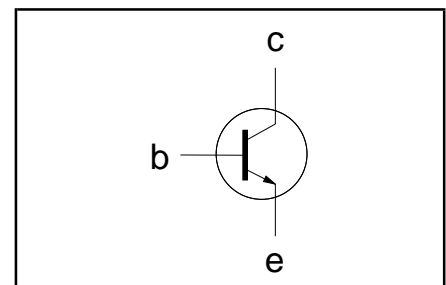
PINNING - SOT223

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector (tab)

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector to emitter voltage	$V_{BE} = 0\text{ V}$	-	700	V
V_{CEO}	Collector to emitter voltage (open base)		-	400	V
V_{CBO}	Collector to base voltage (open emitter)		-	700	V
I_C	Collector current (DC)		-	1.0	A
I_{CM}	Collector current peak value		-	2.0	A
I_B	Base current (DC)		-	0.5	A
I_{BM}	Base current peak value		-	1.0	A
P_{tot}	Total power dissipation	$T_{sp} \leq 25\text{ °C}$	-	6	W
T_{stg}	Storage temperature		-65	150	°C
T_j	Junction temperature		-	150	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-sp}$	Junction to solder point		-	20	K/W
$R_{th\ j-a}$	Junction to ambient	pcb mounted pad areas as in Fig. 23)			
		pcb mounted, minimum footprint	70	-	K/W
		Mounted on 50x34x2mm aluminium PCB	30	-	K/W

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STATIC CHARACTERISTICS $T_{sp} = 25\text{ °C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}, I_{CBO} I_{CES}	Collector cut-off current ¹	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ °C}$	-	2.5 15	100 500	μA μA
I_{CEO} I_{EBO} $V_{CEOsust}$	Collector cut-off current Emitter cut-off current Collector-emitter sustaining voltage	$V_{CE} = V_{CESMmax}(400\text{V})$ $V_{EB} = 9\text{ V}; I_C = 0\text{ A}$ $I_B = 0\text{ A}; I_C = 10\text{ mA};$ $L = 25\text{ mH}$	- - 400	- 0.02 -	100 100 -	μA μA V
V_{CEsat} V_{BEsat}	Collector-emitter saturation voltage Base-emitter saturation voltage	$I_C = 0.75\text{ A}; I_B = 0.15\text{ mA}$ $I_C = 0.75\text{ A}; I_B = 0.15\text{ mA}$	- -	0.23 0.95	1.0 1.3	V V
h_{FE} h_{FE} h_{FE}	DC current gain	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$ $I_C = 100\text{ mA}; V_{CE} = 5\text{ V}$ $I_C = 0.75\text{ A}; V_{CE} = 5\text{ V}$	11 12.5 9	20 21 14	27 31 20	

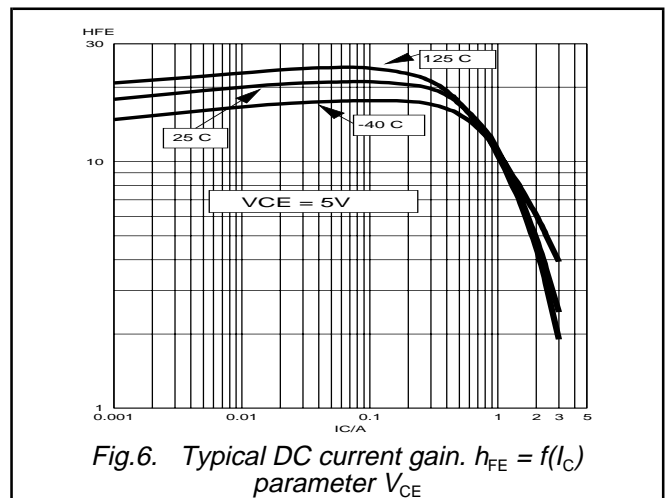
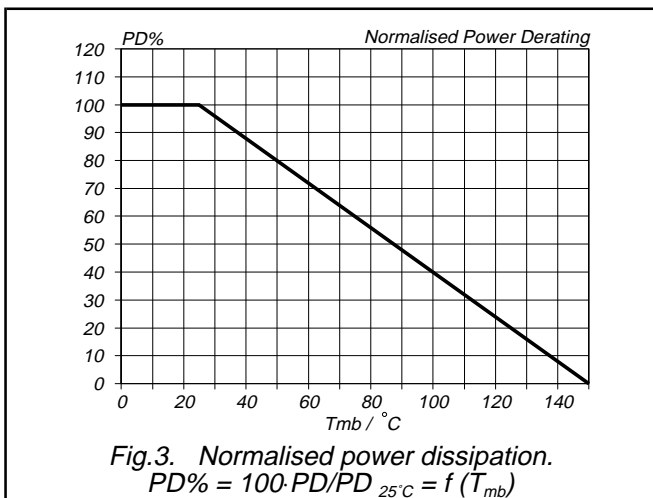
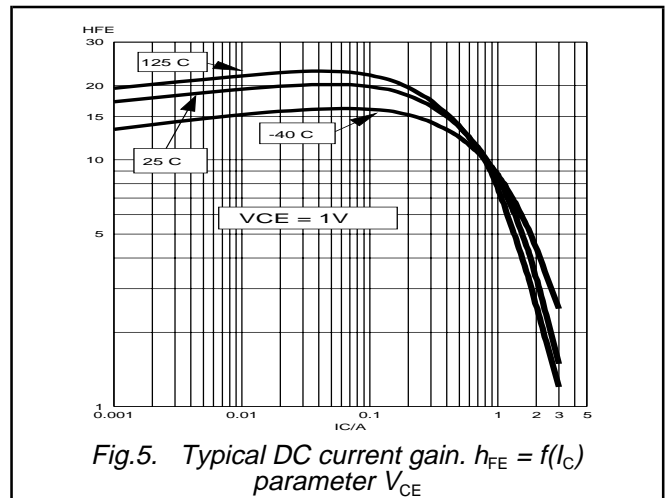
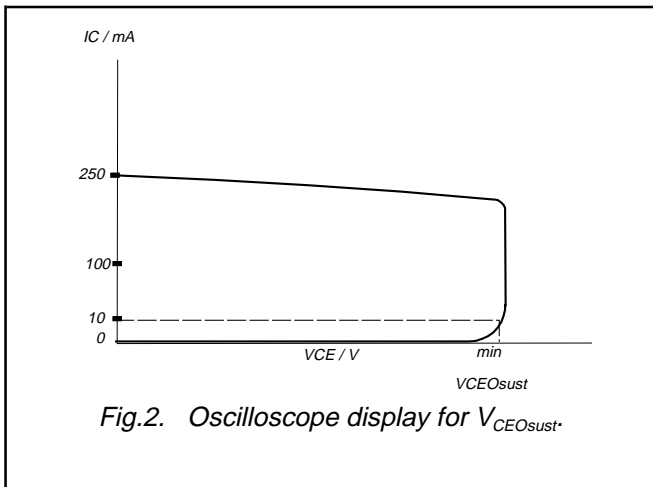
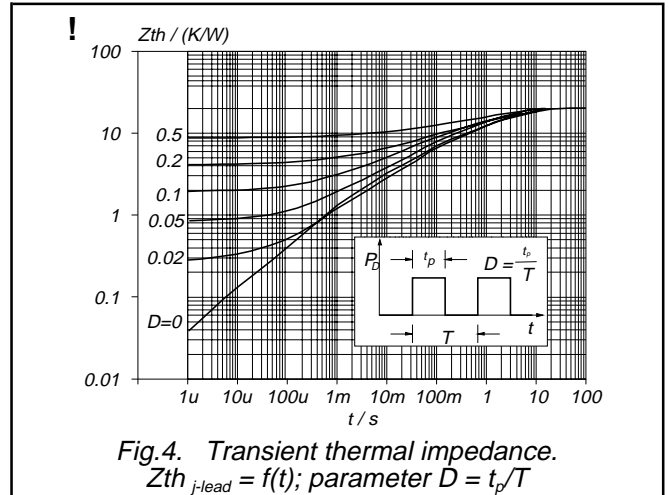
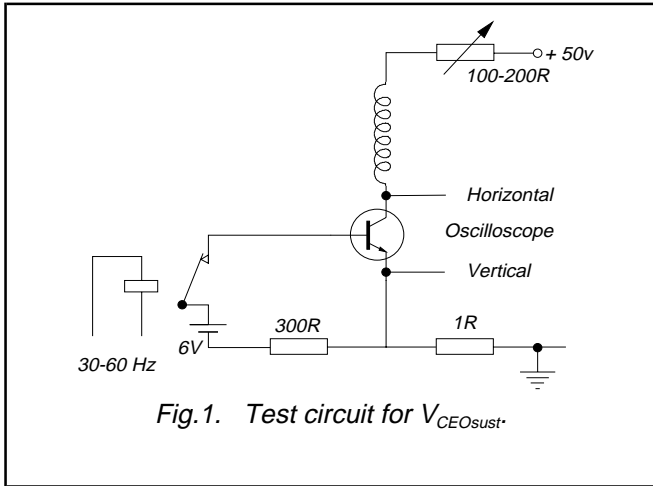
DYNAMIC CHARACTERISTICS $T_{sp} = 25\text{ °C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
t_{on} t_s t_f	Switching times (resistive load) Turn-on time Turn-off storage time Turn-off fall time	$I_{Con} = 1.0\text{ A}; I_{Bon} = -I_{Boff} = 200\text{ mA};$ $R_L = 75\text{ ohms}; V_{BB2} = 4\text{ V};$	0.65 0.88 250	0.88 1.2 338	μs μs ns
t_s t_f	Switching times (inductive load) Turn-off storage time Turn-off fall time	$I_{Con} = 1.0\text{ A}; I_{Bon} = 200\text{ mA}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}$	0.51 50	0.7 70	μs ns
t_s t_f	Switching times (inductive load) Turn-off storage time Turn-off fall time	$I_{Con} = 1.0\text{ A}; I_{Bon} = 200\text{ mA}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}; T_j = 100\text{ °C}$	- -	1.4 130	μs ns

¹ Measured with half sine-wave voltage (curve tracer).

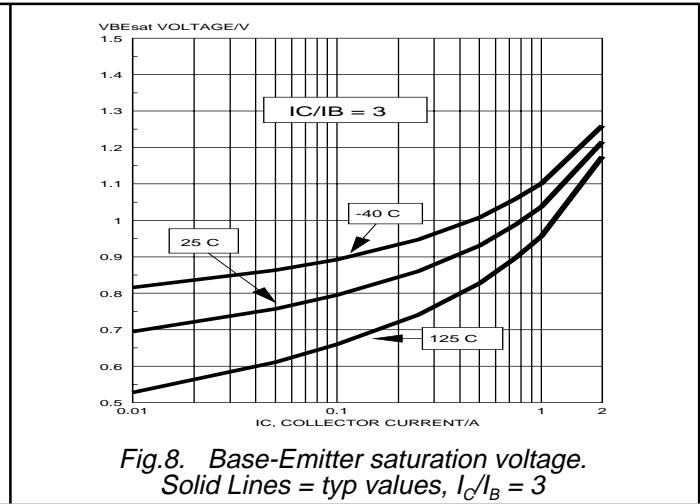
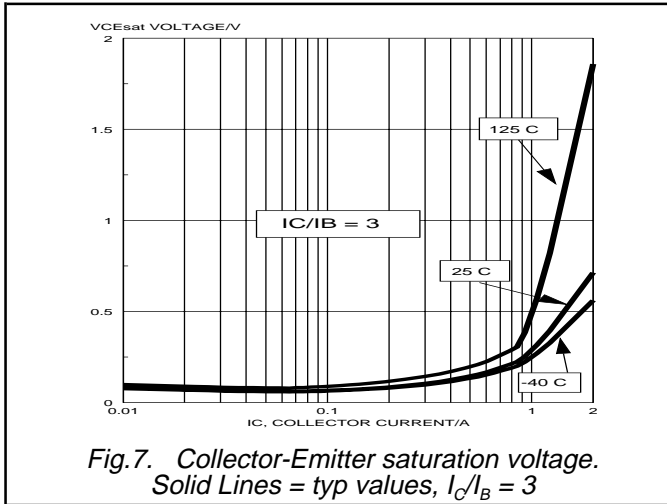
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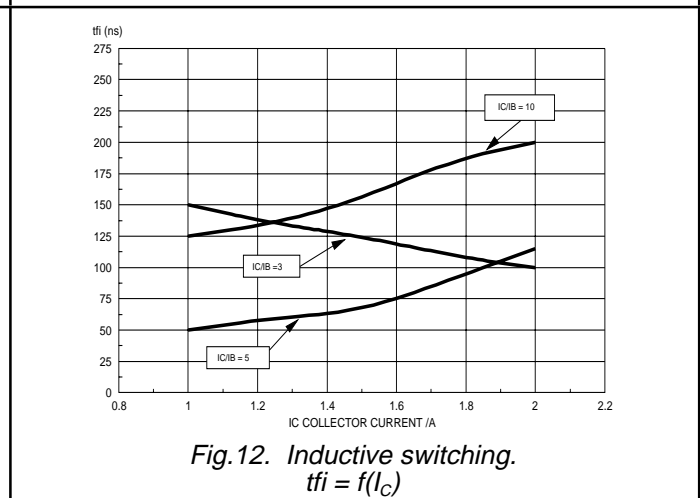
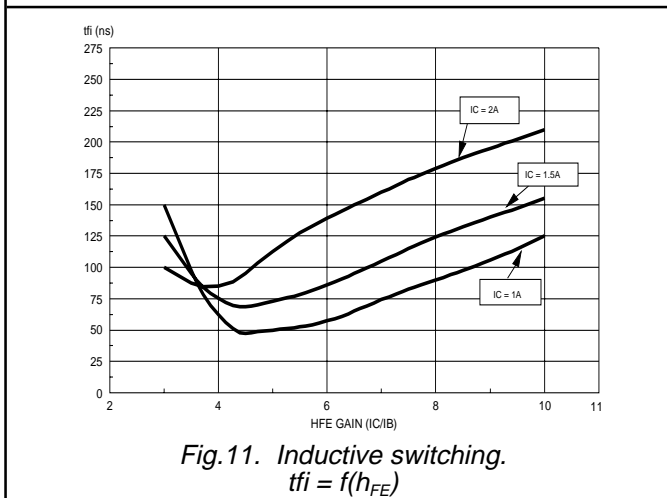
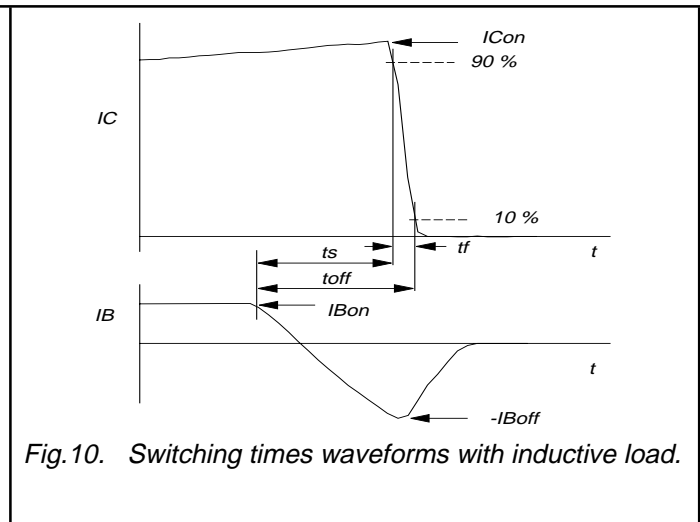
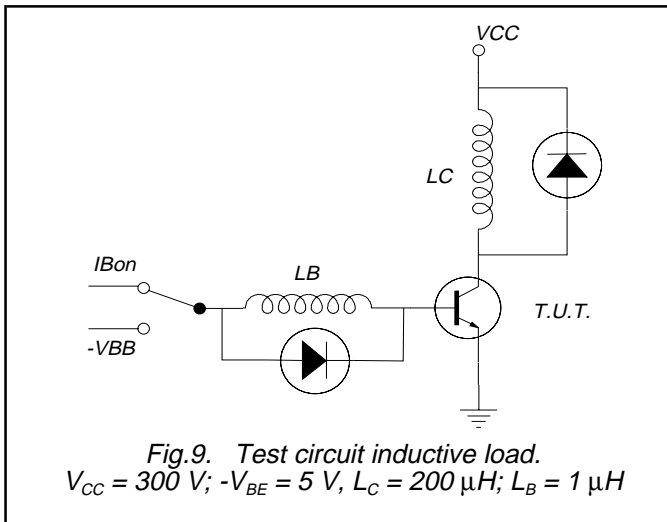


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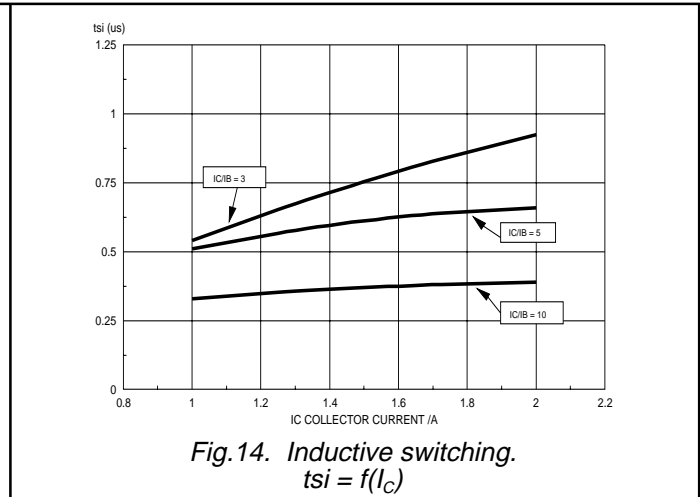
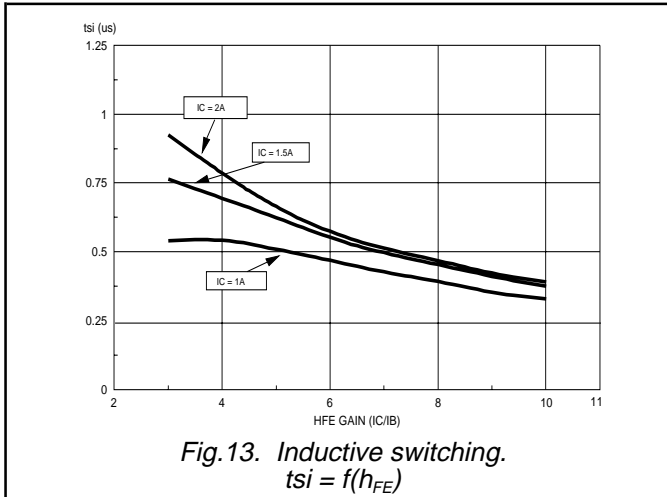


INDUCTIVE SWITCHING

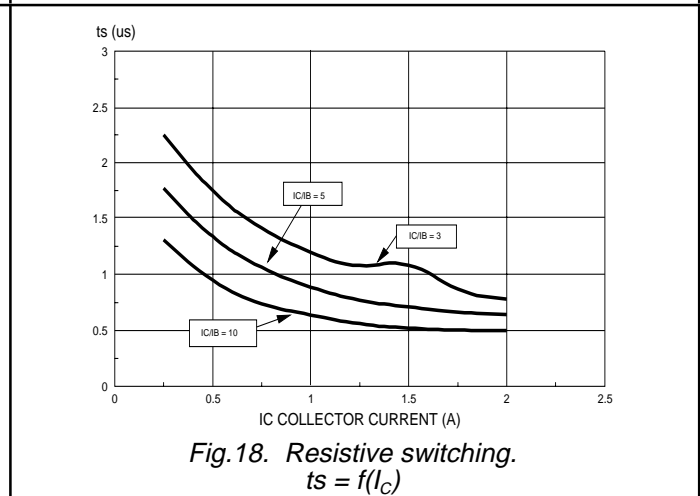
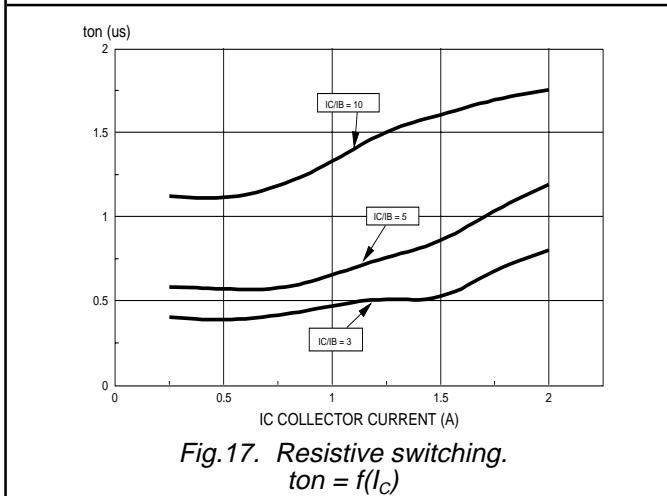
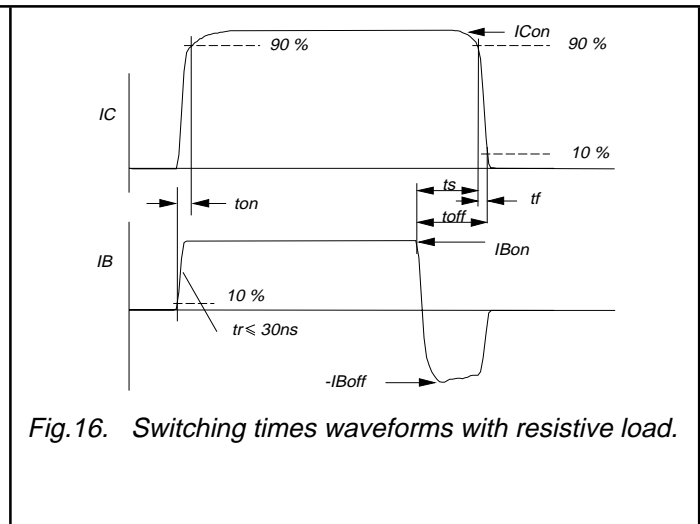
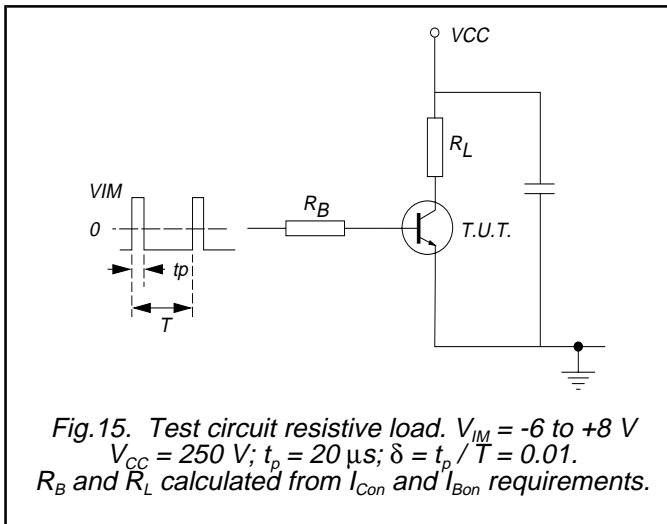


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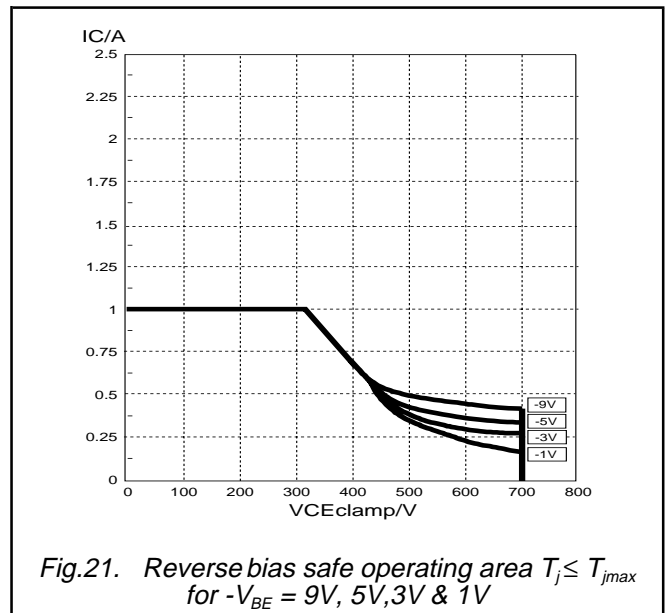
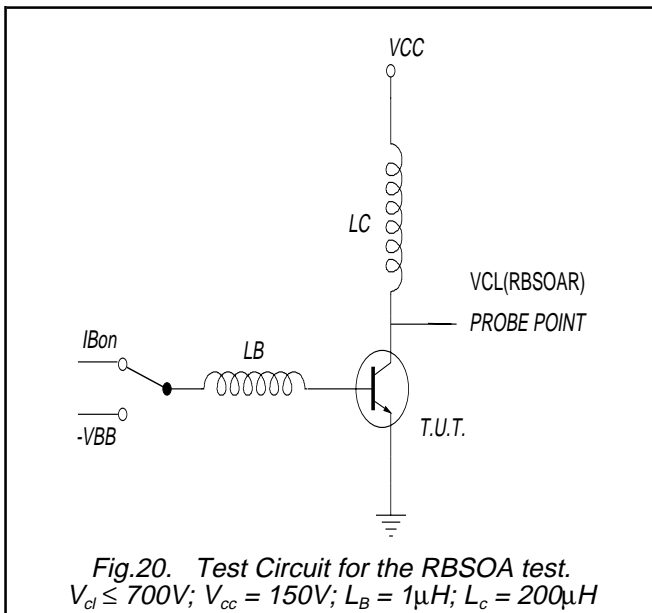
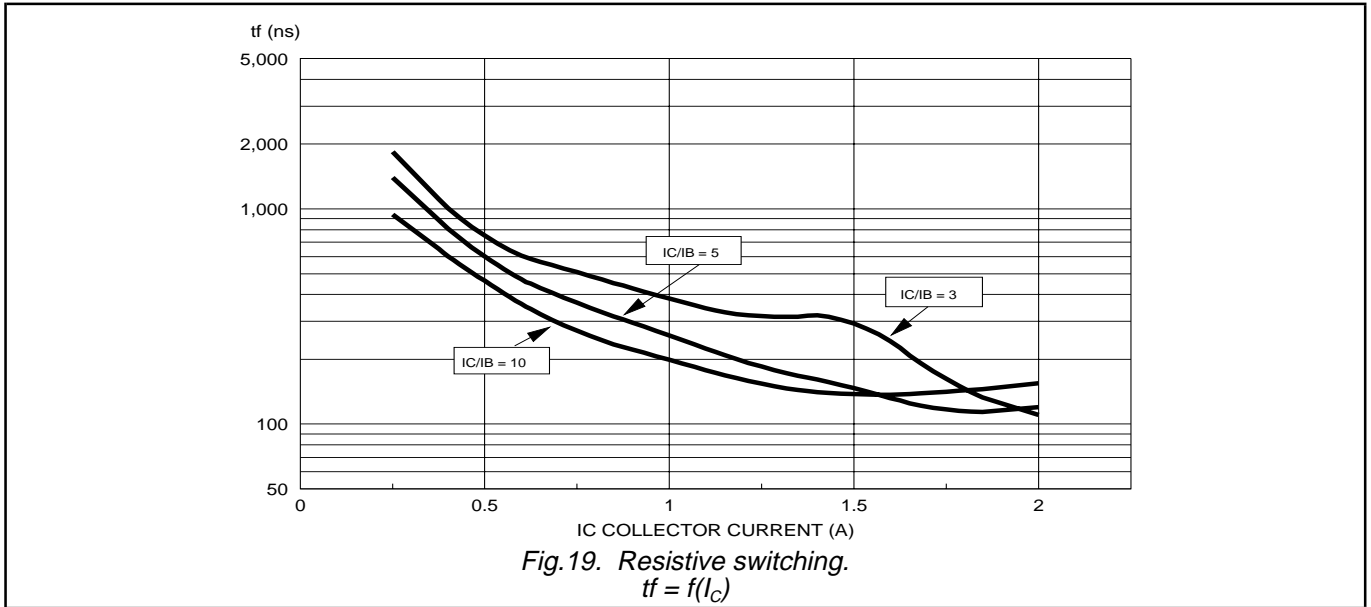


RESISTIVE SWITCHING

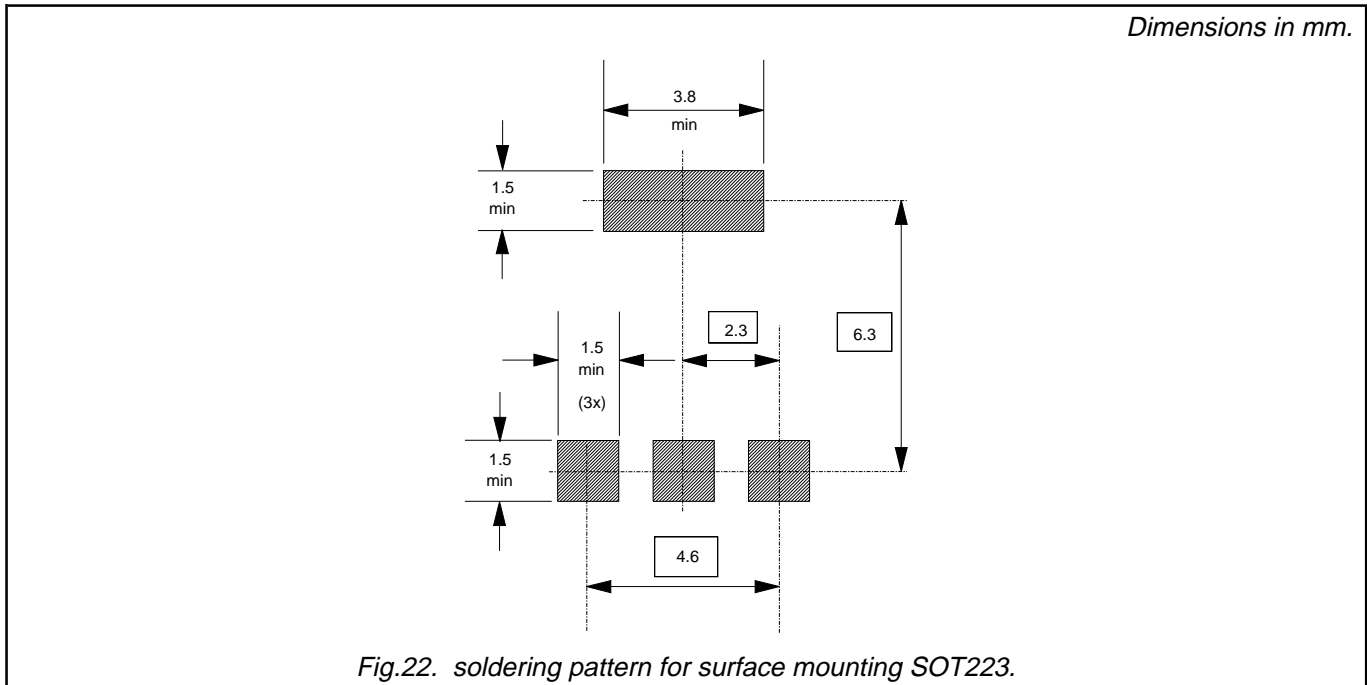


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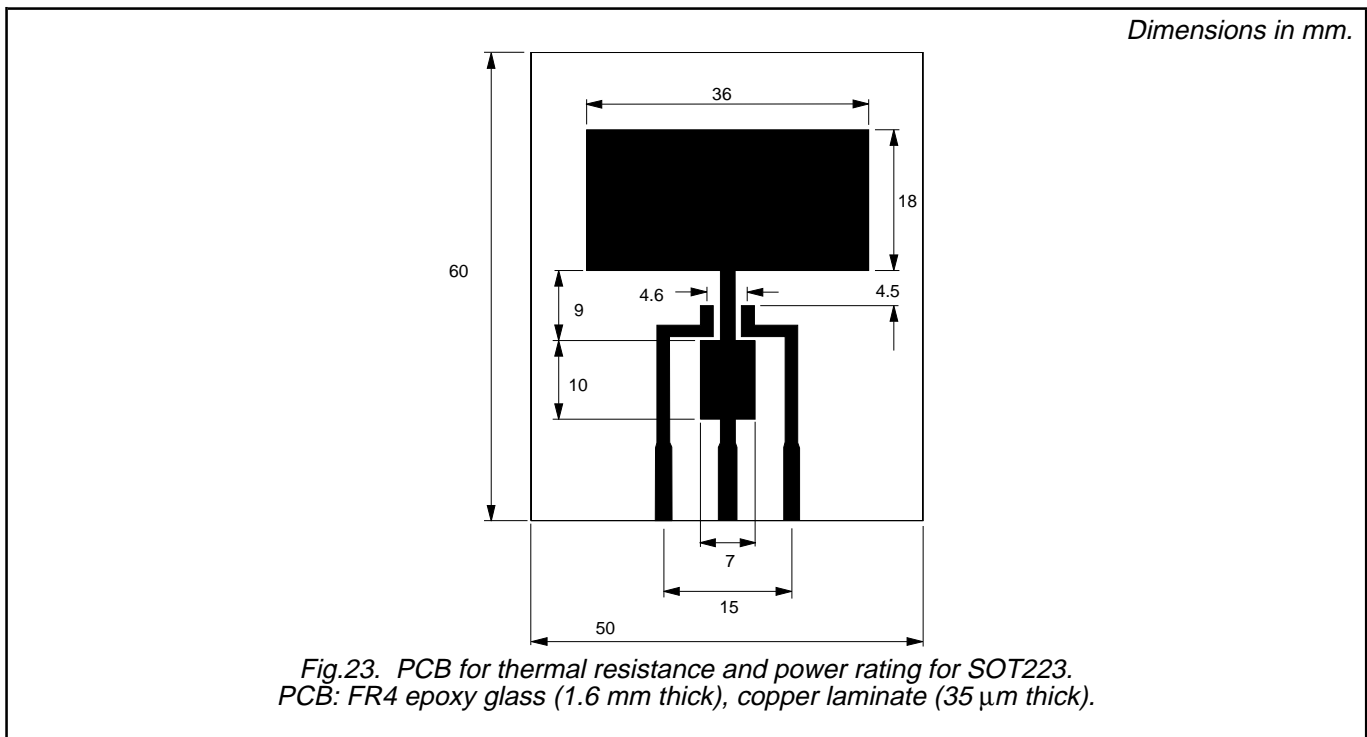
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MOUNTING INSTRUCTIONS



PRINTED CIRCUIT BOARD



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MECHANICAL DATA

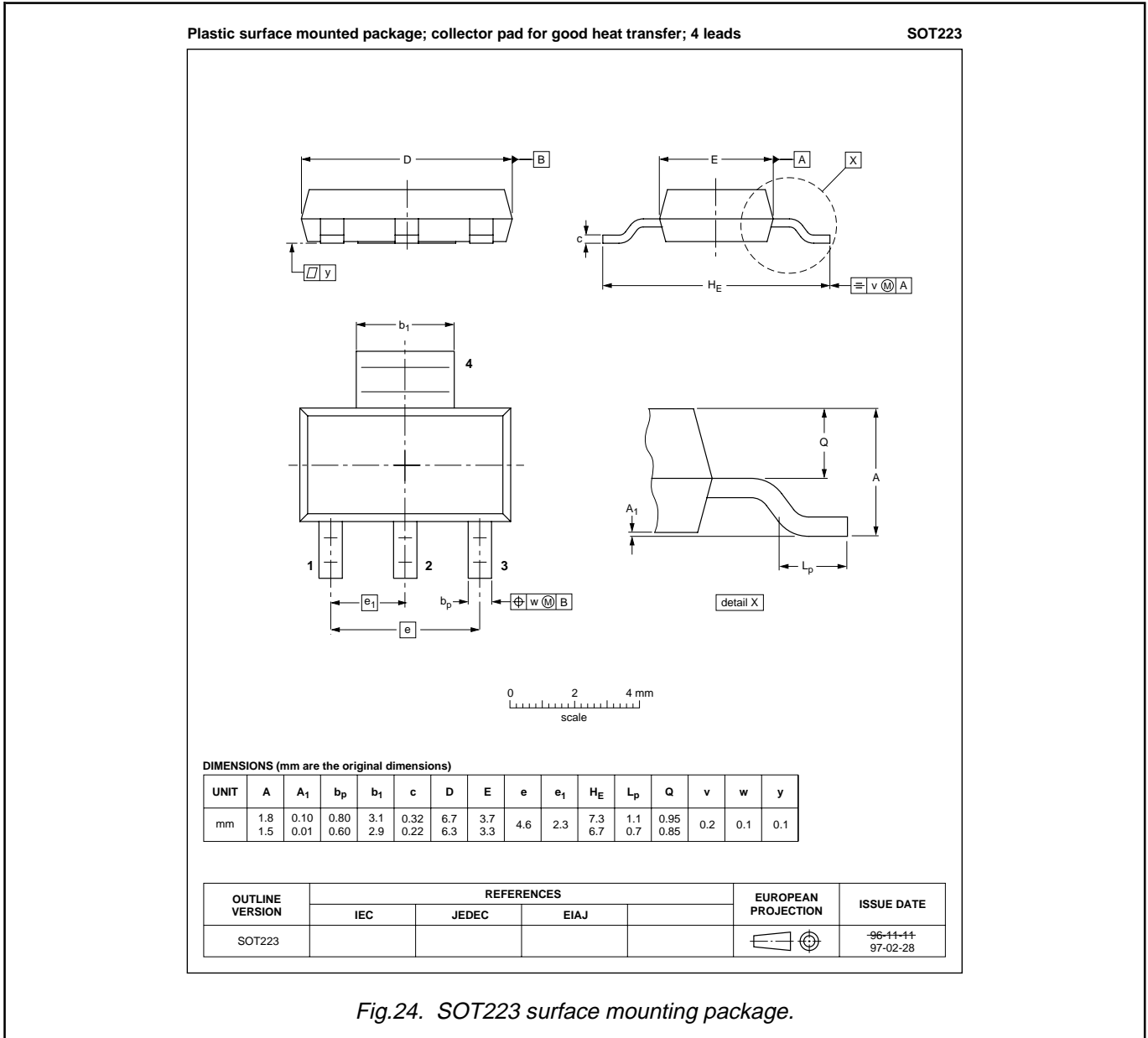


Fig.24. SOT223 surface mounting package.

Notes

1. This product is supplied in anti-static packaging. The gate-source input must be protected against static discharge during transport or handling.
2. Refer to Discrete Semiconductor Packages, Data Handbook SC18.
3. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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